

MGFC41V3642

3.6~4.2GHz BAND 12W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC41V3642 is an internally impedance-matched GaAs power FET especially designed for use in 3.6~4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

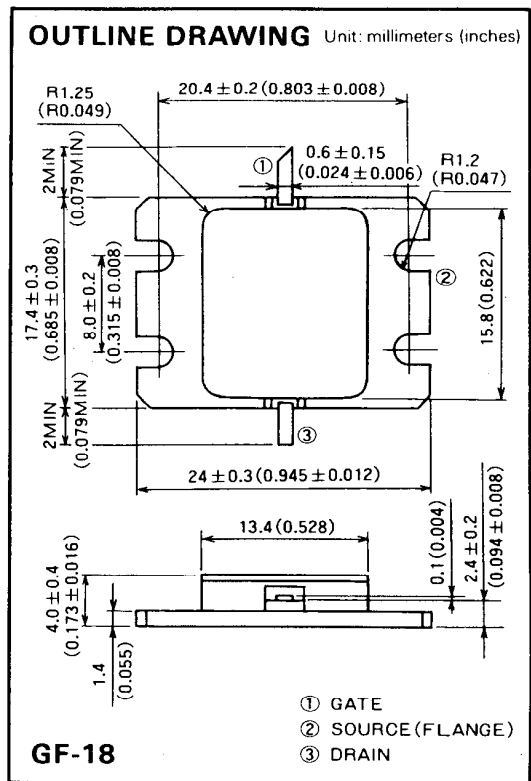
- Class A operation
- Internally matched to 50Ω system
- High output power
 $P_{1dB} = 14W(TYP) @ 3.6\sim 4.2GHz$
- High power gain
 $G_{LP} = 12.5dB(TYP) @ 3.6\sim 4.2GHz$
- High power added efficiency
 $\eta_{add} = 40\%(TYP) @ 3.6\sim 4.2GHz, P_{1dB}$
- Hermetically sealed metal-ceramic package
- Low distortion [Item: -51]
 $IM_3 = -45 dBc(TYP) @ P_o = 30(dBm) S.C.L.$

APPLICATION

- Item-01: 3.6~4.2 GHz band power amplifier
- Item-51: Digital radio communication

QUALITY GRADE

- IG



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter	Ratings	Unit
V _{GD0}	Gate to drain voltage	-15	V
V _{GSO}	Gate to source voltage	-15	V
I _D	Drain current	12	A
I _{GR}	Reverse gate current	-30	mA
I _{GF}	Forward gate current	63	mA
P _T	Total power dissipation *1	57.7	W
T _{ch}	Channel temperature	175	°C
T _{stg}	Storage temperature	-65 ~ +175	°C

*1: T_c = 25°C

RECOMMENDED BIAS CONDITIONS

- V_{DS} = 10V
- I_D = 3.4A
- R_g = 50Ω
- Refer to Bias Procedure

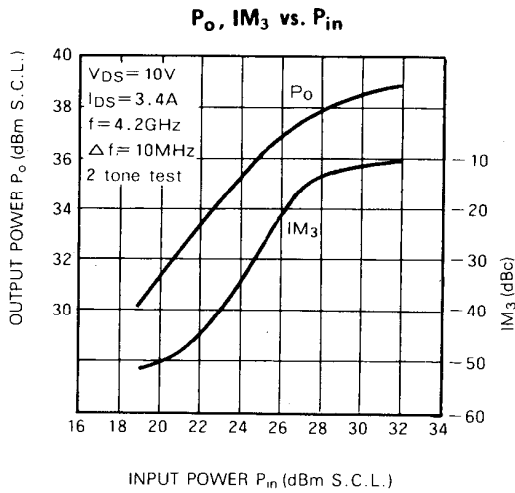
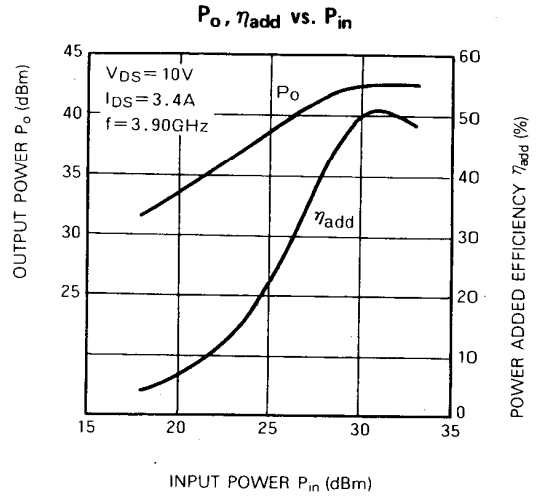
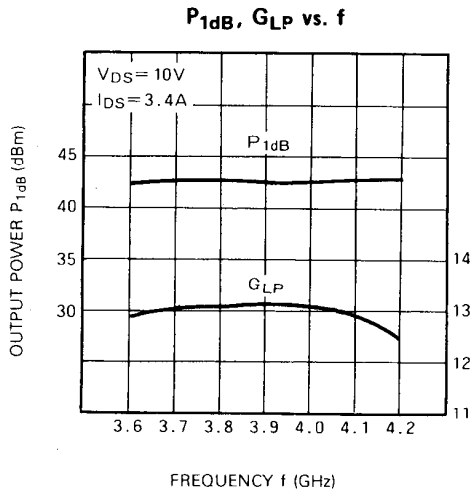
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
I _{DSS}	Saturated drain current	V _{DS} = 3V, V _{GS} = 0V	—	—	12	A	
g _m	Transconductance	V _{DS} = 3V, I _D = 3.0A	—	3.0	—	S	
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} = 3V, I _D = 30mA	—	—	-5	V	
P _{1dB}	Output power at 1dB gain compression	V _{DS} = 10V, I _D = 3.4A, f = 3.6~4.2GHz	40	41.5	—	dBm	
G _{LP}	Linear power gain		11.0	12.5	—	dB	
I _D	Drain current		—	3.3	—	A	
η _{add}	Power added efficiency		—	40	—	%	
IM ₃	3rd order IM distortion *1		-42	-45	—	dBc	
R _{th(ch-c)}	Thermal resistance *2		ΔV _f method	—	—	2.6	°C/W

*1: Item-51, 2-tone test P_o = 30 dBm Single Carrier Level f = 4.2 GHz Δf = 10 MHz *2: Channel to case

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TYPICAL CHARACTERISTICS (Ta=25°C)



S PARAMETERS (Ta=25°C, V_{DS}=10V, I_{DS}=3.4A)

f (GHz)	S Parameters (TYP.)							
	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
3.6	0.48	-168	4.13	57	0.042	10	0.45	-23
3.7	0.47	155	4.29	32	0.052	-21	0.34	-45
3.8	0.44	121	4.45	6	0.052	-45	0.26	-73
3.9	0.40	86	4.39	-20	0.058	-75	0.23	-115
4.0	0.35	42	4.34	-46	0.060	-101	0.22	-160
4.1	0.31	-11	4.17	-73	0.066	-123	0.28	166
4.2	0.34	-70	3.70	-100	0.057	-150	0.29	140